

74CBTLV3253

Dual 1-of-4 multiplexer/demultiplexer

Rev. 01 — 8 January 2010

Product data sheet

1. General description

The 74CBTLV3253 provides a dual 1-of-4 high-speed multiplexer/demultiplexer with two common select inputs (S0, S1) and two output enable inputs ($\overline{1OE}$, $\overline{2OE}$). The low ON resistance of the switch allows inputs to be connected to outputs without adding propagation delay or generating additional ground bounce noise. When pin $\overline{nOE} = \text{LOW}$, one of the four switches is selected (low-impedance ON-state) with pins S0 and S1. When pin $\overline{nOE} = \text{HIGH}$, all switches are in the high-impedance OFF-state, independent of pins S0 and S1.

To ensure the high-impedance OFF-state during power-up or power-down, \overline{nOE} should be tied to the V_{CC} through a pull-up resistor. The minimum value of the resistor is determined by the current-sinking capability of the driver.

Schmitt trigger action at control input makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 2.3 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features

- Supply voltage range from 2.3 V to 3.6 V
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM AEC-Q100-011 revision B exceeds 1000 V
- 5 Ω switch connection between two ports
- Rail to rail switching on data I/O ports
- CMOS low power consumption
- Latch-up performance exceeds 250 mA per JESD78B Class I level A
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74CBTLV3253D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74CBTLV3253DS	-40 °C to +85 °C	SSOP16 ^[1]	plastic shrink small outline package; 16 leads; body width 3.9 mm; lead pitch 0.635 mm	SOT519-1
74CBTLV3253PW	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74CBTLV3253BQ	-40 °C to +125 °C	DHVQFN16	plastic dual-in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1

[1] Also known as QSOP16.

4. Functional diagram

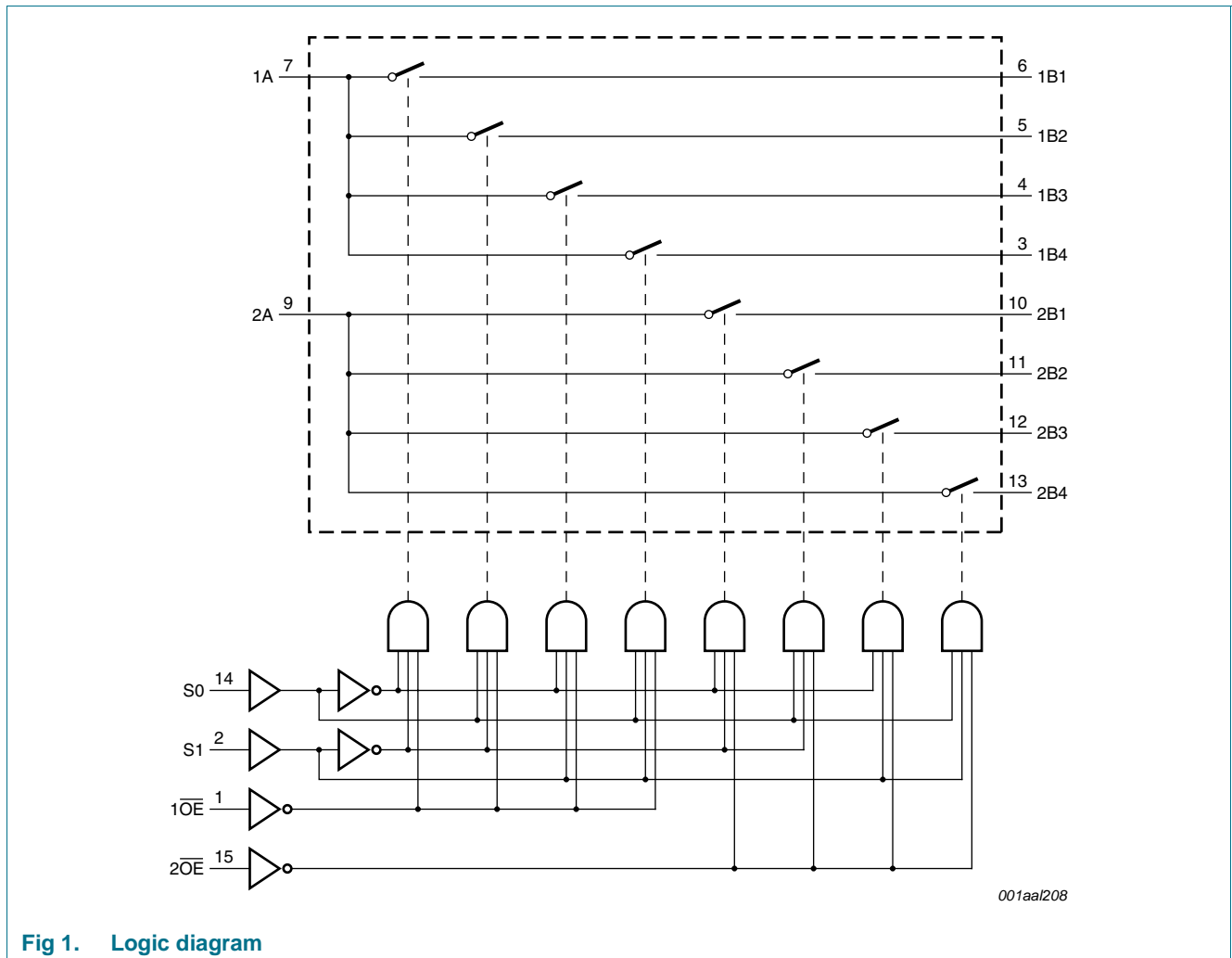
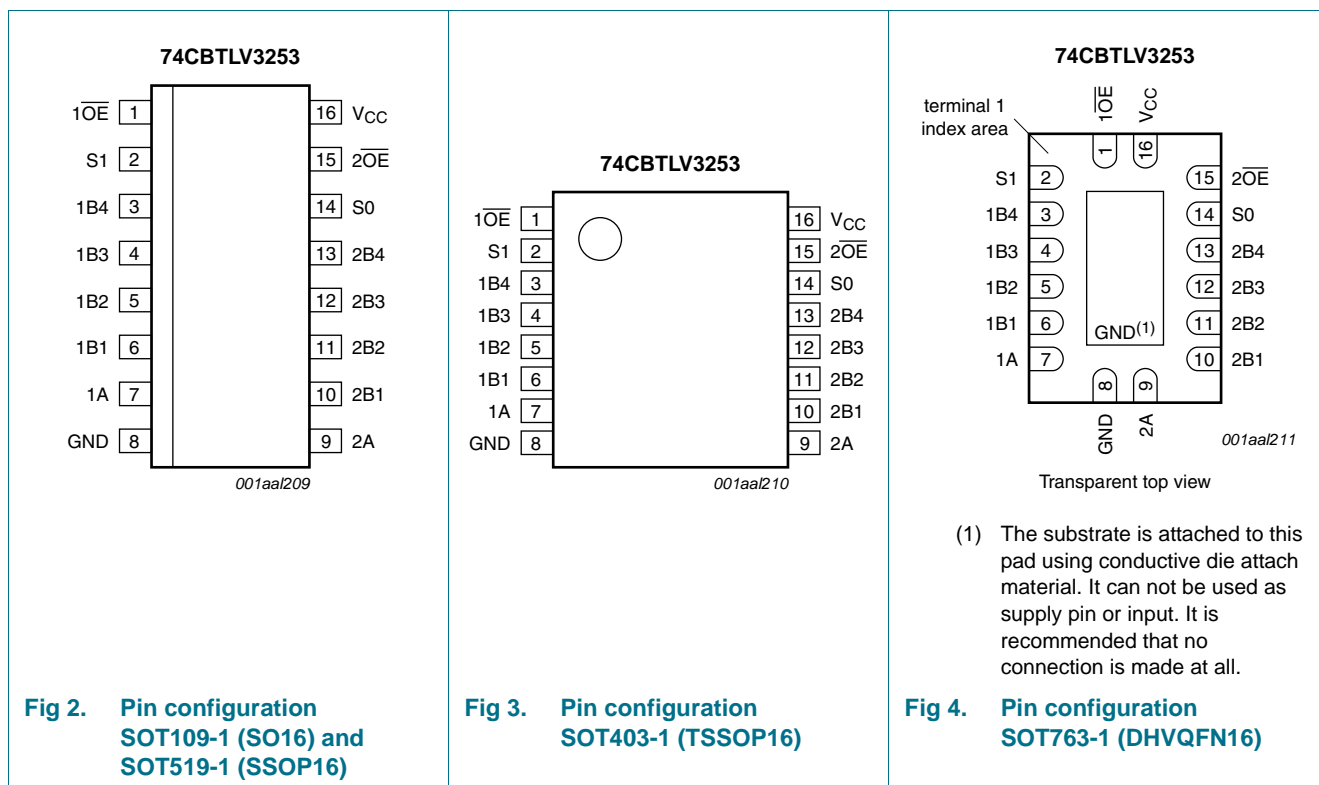


Fig 1. Logic diagram

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
10E, 2OE	1, 15	output enable input (active LOW)
S0, S1	14, 2	select input
1B1 to 1B4	6, 5, 4, 3	B input/output
2B1 to 2B4	10, 11, 12, 13	B input/output
GND	8	ground (0 V)
1A, 2A	7, 9	A input/output
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table^[1]

Inputs				Function switch
1OE	2OE	S1	S0	
X	H	X	X	disconnect 2A and 2Bn
H	X	X	X	disconnect 1A and 1Bn
L	L	L	L	1A to 1B1 and 2A to 2B1
L	L	L	H	1A to 1B2 and 2A to 2B2
L	L	H	L	1A to 1B3 and 2A to 2B3
L	L	H	H	1A to 1B4 and 2A to 2B4

[1] H = HIGH voltage level; L = LOW voltage level.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
V_I	input voltage	control inputs	^[1] -0.5	+4.6	V
V_{SW}	switch voltage	enable and disable mode	^[2] -0.5	$V_{CC} + 0.5$	V
I_{IK}	input clamping current	$V_I < -0.5$ V	-50	-	mA
I_{SK}	switch clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	-	±50	mA
I_{SW}	switch current	$V_{SW} = 0$ V to V_{CC}	-	±128	mA
I_{CC}	supply current		-	+100	mA
I_{GND}	ground current		-100	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	^[3] -	500	mW

[1] The minimum input voltage rating may be exceeded if the input clamping current ratings are observed.

[2] The switch voltage ratings may be exceeded if switch clamping current ratings are observed

[3] For SSOP16 and TSSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
For DHVQFN16 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		2.3	3.6	V
V_I	input voltage		0	3.6	V
V_{SW}	switch voltage	enable and disable mode	0	V_{CC}	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.3$ V to 3.6 V	^[1] 0	200	ns/V

[1] Applies to control signal levels.

9. Static characteristics

Table 6. Static characteristics

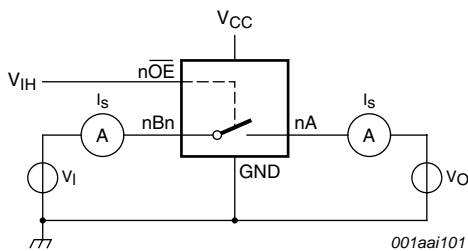
At recommended operating conditions voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	-	0.9	V
I _I	input leakage current	pin n $\overline{\text{OE}}$; V _I = GND to V _{CC} ; V _{CC} = 3.6 V	-	-	±1	-	±20	μA
I _{S(OFF)}	OFF-state leakage current	V _{CC} = 3.6 V; see Figure 5	-	-	±1	-	±20	μA
I _{S(ON)}	ON-state leakage current	V _{CC} = 3.6 V; see Figure 6	-	-	±1	-	±20	μA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±10	-	±50	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{SW} = GND or V _{CC} ; V _{CC} = 3.6 V	-	-	10	-	50	μA
ΔI _{CC}	additional supply current	pin n $\overline{\text{OE}}$; V _I = V _{CC} - 0.6 V; [2] V _{SW} = GND or V _{CC} ; V _{CC} = 3.6 V	-	-	300	-	2000	μA
C _I	input capacitance	pin n $\overline{\text{OE}}$; V _{CC} = 3.3 V; V _I = 0 V to 3.3 V	-	0.9	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance	V _{CC} = 3.3 V; V _I = 0 V to 3.3 V	-	5.2	-	-	-	pF
C _{S(ON)}	ON-state capacitance	V _{CC} = 3.3 V; V _I = 0 V to 3.3 V	-	20.0	-	-	-	pF

[1] All typical values are measured at T_{amb} = 25 °C.

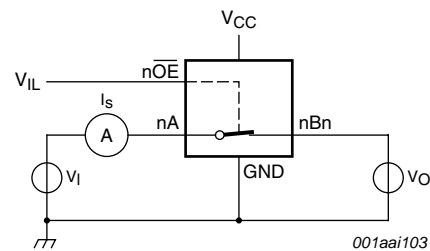
[2] One input at 3 V, other inputs at V_{CC} or GND.

9.1 Test circuits



V_I = V_{CC} or GND and V_O = GND or V_{CC}.

Fig 5. Test circuit for measuring OFF-state leakage current (one switch)



V_I = V_{CC} or GND and V_O = open circuit.

Fig 6. Test circuit for measuring ON-state leakage current (one switch)

9.2 ON resistance

Table 7. Resistance R_{ON}

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions	$T_{amb} = -40\text{ }^{\circ}\text{C to }+85\text{ }^{\circ}\text{C}$			$T_{amb} = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$		Unit
			Min	Typ ^[1]	Max	Min	Max	
R_{ON}	ON resistance	$V_{CC} = 2.3\text{ V to }2.7\text{ V};$ see Figure 8 to Figure 10						
		$I_{SW} = 64\text{ mA}; V_I = 0\text{ V}$	-	4.2	8.0	-	15.0	Ω
		$I_{SW} = 24\text{ mA}; V_I = 0\text{ V}$	-	4.2	8.0	-	15.0	Ω
		$I_{SW} = 15\text{ mA}; V_I = 1.7\text{ V}$	-	8.4	40.0	-	60.0	Ω
		$V_{CC} = 3.0\text{ V to }3.6\text{ V};$ see Figure 11 to Figure 13						
		$I_{SW} = 64\text{ mA}; V_I = 0\text{ V}$	-	4.0	7.0	-	11.0	Ω
		$I_{SW} = 24\text{ mA}; V_I = 0\text{ V}$	-	4.0	7.0	-	11.0	Ω
		$I_{SW} = 15\text{ mA}; V_I = 2.4\text{ V}$	-	6.2	15.0	-	25.5	Ω

[1] Typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$ and nominal V_{CC} .

[2] Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

9.3 ON resistance test circuit and graphs

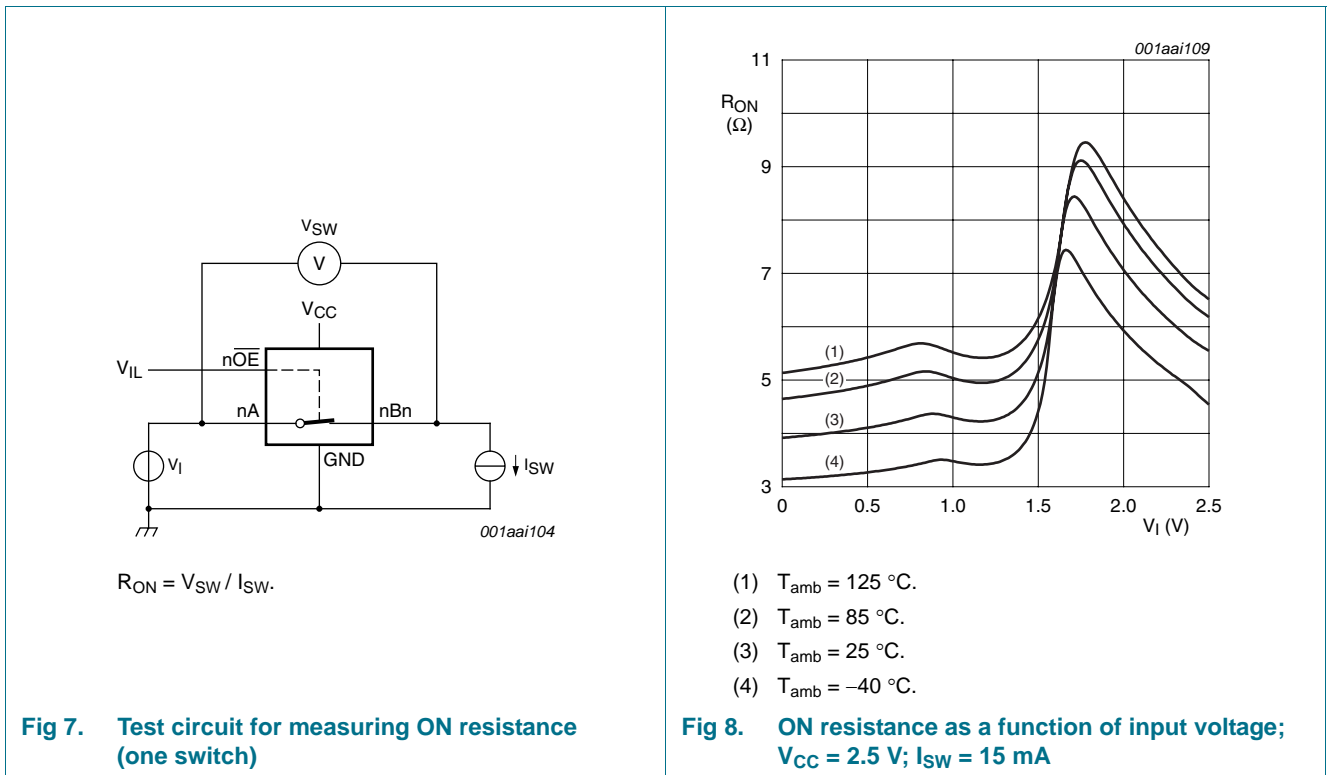
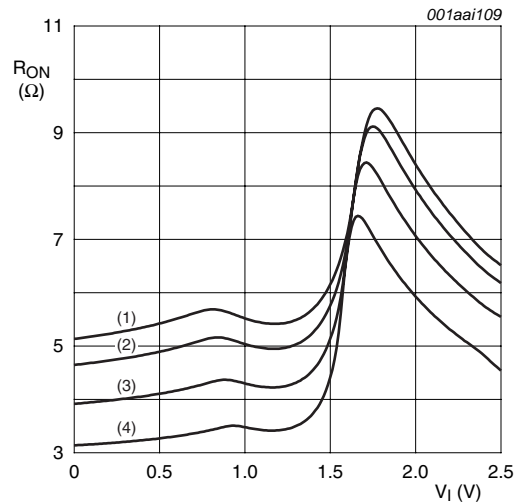
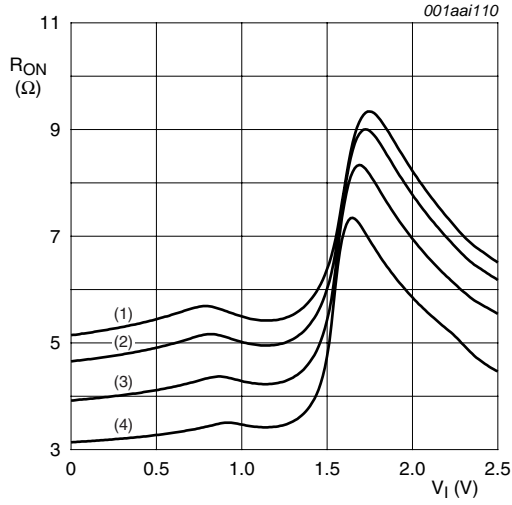


Fig 7. Test circuit for measuring ON resistance (one switch)



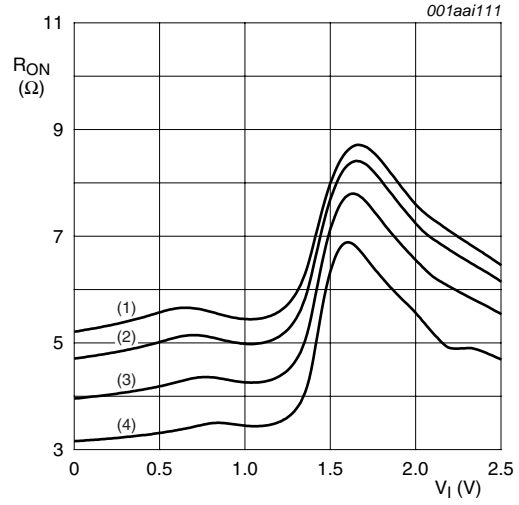
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}$.

Fig 8. ON resistance as a function of input voltage; $V_{CC} = 2.5\text{ V}; I_{SW} = 15\text{ mA}$



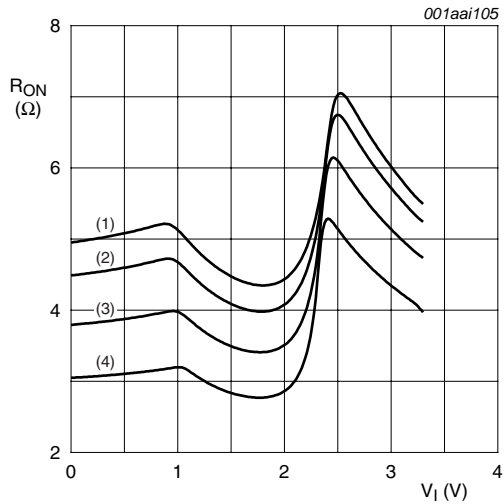
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 9. ON resistance as a function of input voltage; $V_{CC} = 2.5\text{ V}; I_{SW} = 24\text{ mA}$



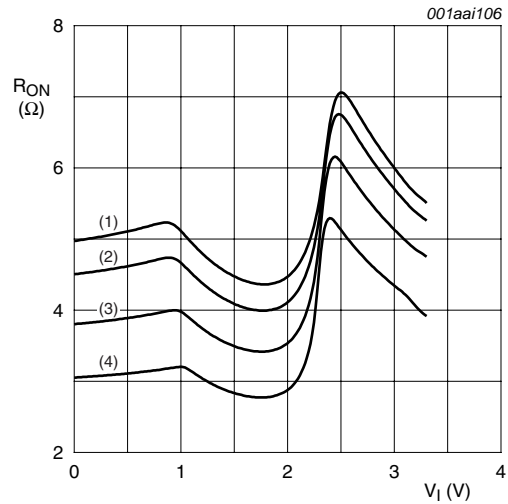
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 10. ON resistance as a function of input voltage; $V_{CC} = 2.5\text{ V}; I_{SW} = 64\text{ mA}$



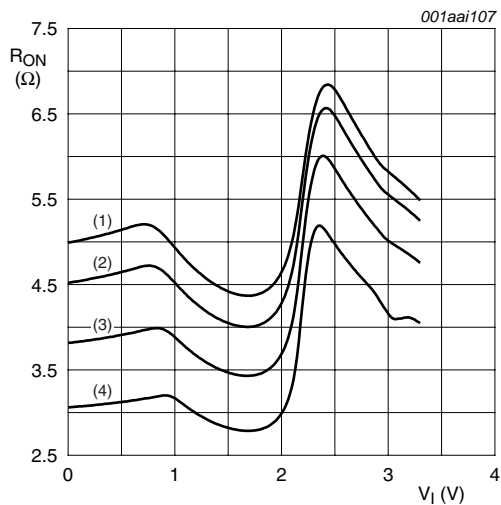
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 11. ON resistance as a function of input voltage; $V_{CC} = 3.3\text{ V}; I_{SW} = 15\text{ mA}$



- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 12. ON resistance as a function of input voltage; $V_{CC} = 3.3\text{ V}; I_{SW} = 24\text{ mA}$



- (1) $T_{amb} = 125\text{ °C}$.
- (2) $T_{amb} = 85\text{ °C}$.
- (3) $T_{amb} = 25\text{ °C}$.
- (4) $T_{amb} = -40\text{ °C}$.

Fig 13. ON resistance as a function of input voltage; $V_{CC} = 3.3\text{ V}$; $I_{SW} = 64\text{ mA}$

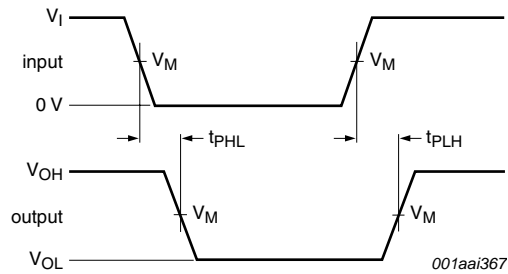
10. Dynamic characteristics

Table 8. Dynamic characteristics
GND = 0 V; for test circuit see Figure 16

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	nA to nBn or nBn to nA; see Figure 14 [2][3]						
		V _{CC} = 2.3 V to 2.7 V	-	-	0.15	-	0.25	ns
		V _{CC} = 3.0 V to 3.6 V	-	-	0.15	-	0.25	ns
		Sn to nA; see Figure 14 [3]						
		V _{CC} = 2.3 V to 2.7 V	1.0	2.2	6.8	1.0	7.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.0	5.5	1.0	6.1	ns
t _{en}	enable time	nOE to nA or nBn; see Figure 15 [4]						
		V _{CC} = 2.3 V to 2.7 V	1.0	2.1	5.0	1.0	5.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	1.9	4.8	1.0	5.3	ns
		Sn to nBn; see Figure 15 [4]						
		V _{CC} = 2.3 V to 2.7 V	1.0	2.1	4.3	1.0	4.7	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	1.9	4.0	1.0	4.4	ns
t _{dis}	disable time	nOE to nA or nBn; see Figure 15 [5]						
		V _{CC} = 2.3 V to 2.7 V	1.0	2.6	5.5	1.0	6.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	3.2	5.4	1.0	5.9	ns
		Sn to nBn; see Figure 15 [5]						
		V _{CC} = 2.3 V to 2.7 V	0.8	2.0	4.8	0.8	5.3	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.0	4.5	1.0	5.0	ns

- [1] All typical values are measured at T_{amb} = 25 °C and at nominal V_{CC}.
- [2] The propagation delay is the calculated RC time constant of the maximum on-state resistance of the switch and the load capacitance, when driven by an ideal voltage source (zero output impedance).
- [3] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [4] t_{en} is the same as t_{PZH} and t_{PZL}.
- [5] t_{dis} is the same as t_{PHZ} and t_{PLZ}.

11. Waveforms



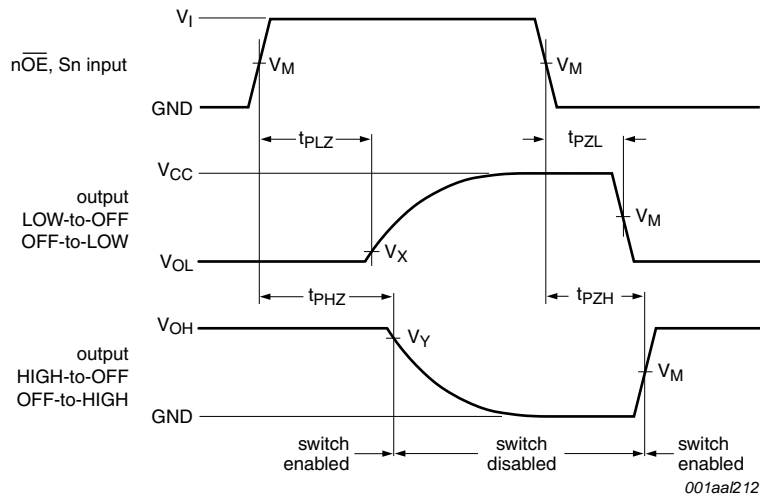
Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 14. The data input (nA or nBn) to output (nBn or nA) propagation delays

Table 9. Measurement points

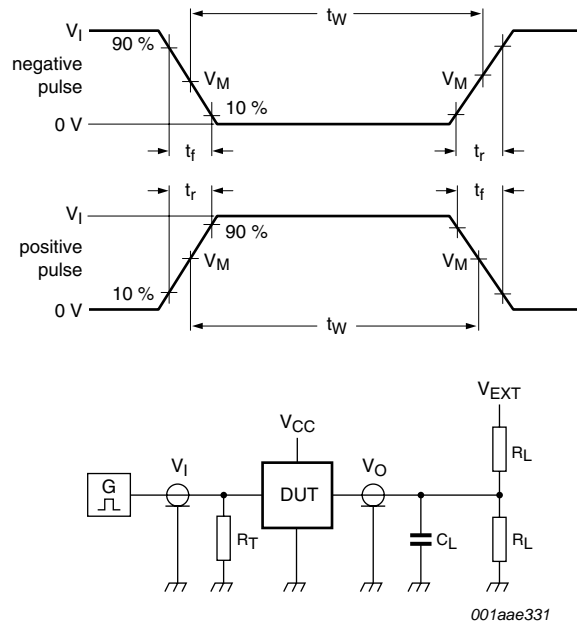
Supply voltage	Input			Output		
V_{CC}	V_M	V_I	$t_r = t_f$	V_M	V_X	V_Y
2.3 V to 2.7 V	$0.5V_{CC}$	V_{CC}	≤ 2.0 ns	$0.5V_{CC}$	$V_{OL} + 0.15$ V	$V_{OH} - 0.15$ V
3.0 V to 3.6 V	$0.5V_{CC}$	V_{CC}	≤ 2.0 ns	$0.5V_{CC}$	$V_{OL} + 0.3$ V	$V_{OH} - 0.3$ V



Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 15. Enable and disable times



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 16. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V_{EXT}		
	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
2.3 V to 2.7 V	30 pF	500 Ω	open	GND	$2V_{CC}$
3.0 V to 3.6 V	50 pF	500 Ω	open	GND	$2V_{CC}$

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

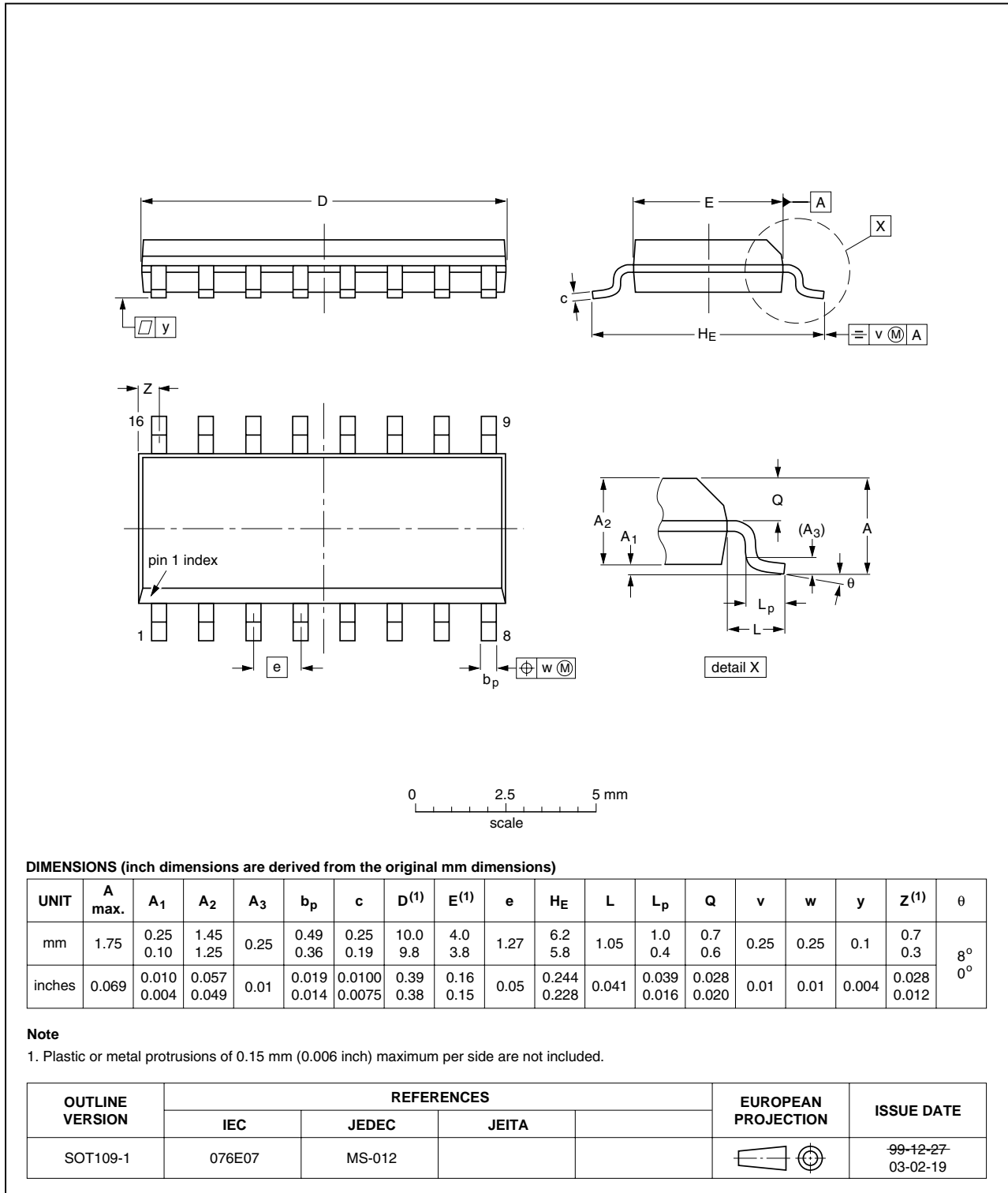


Fig 17. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 3.9 mm; lead pitch 0.635 mm SOT519-1

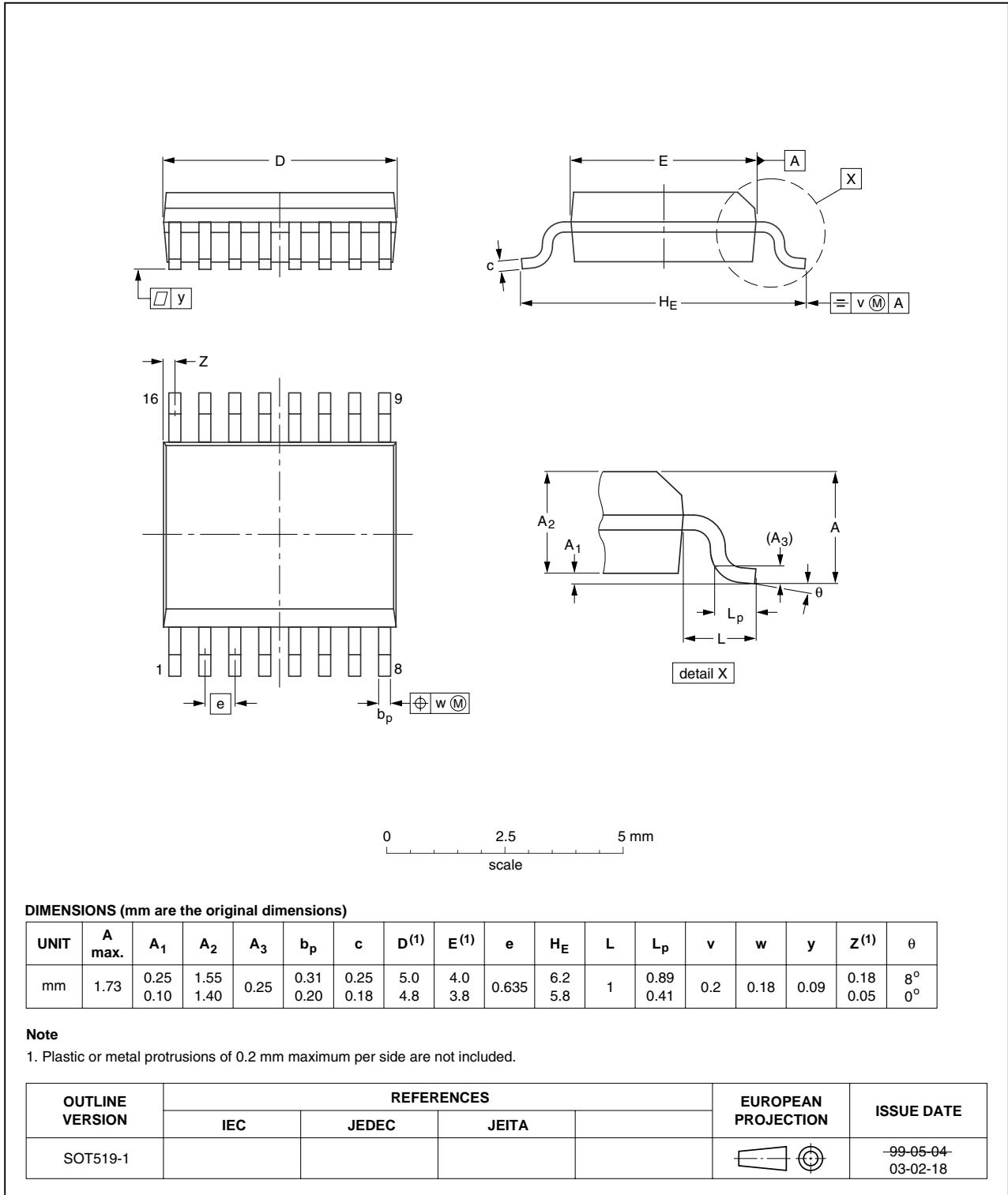


Fig 18. Package outline SOT519-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

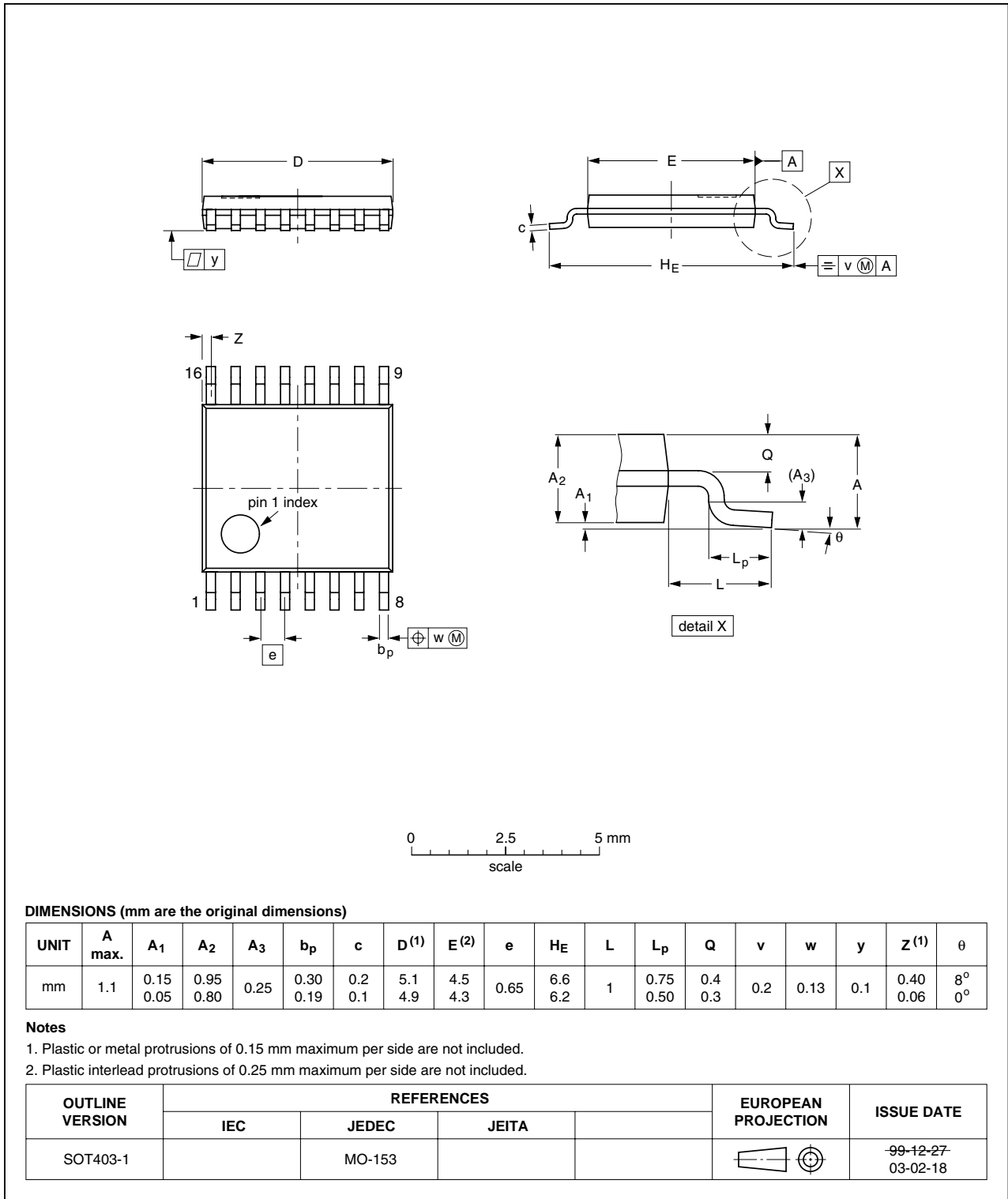


Fig 19. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm

SOT763-1

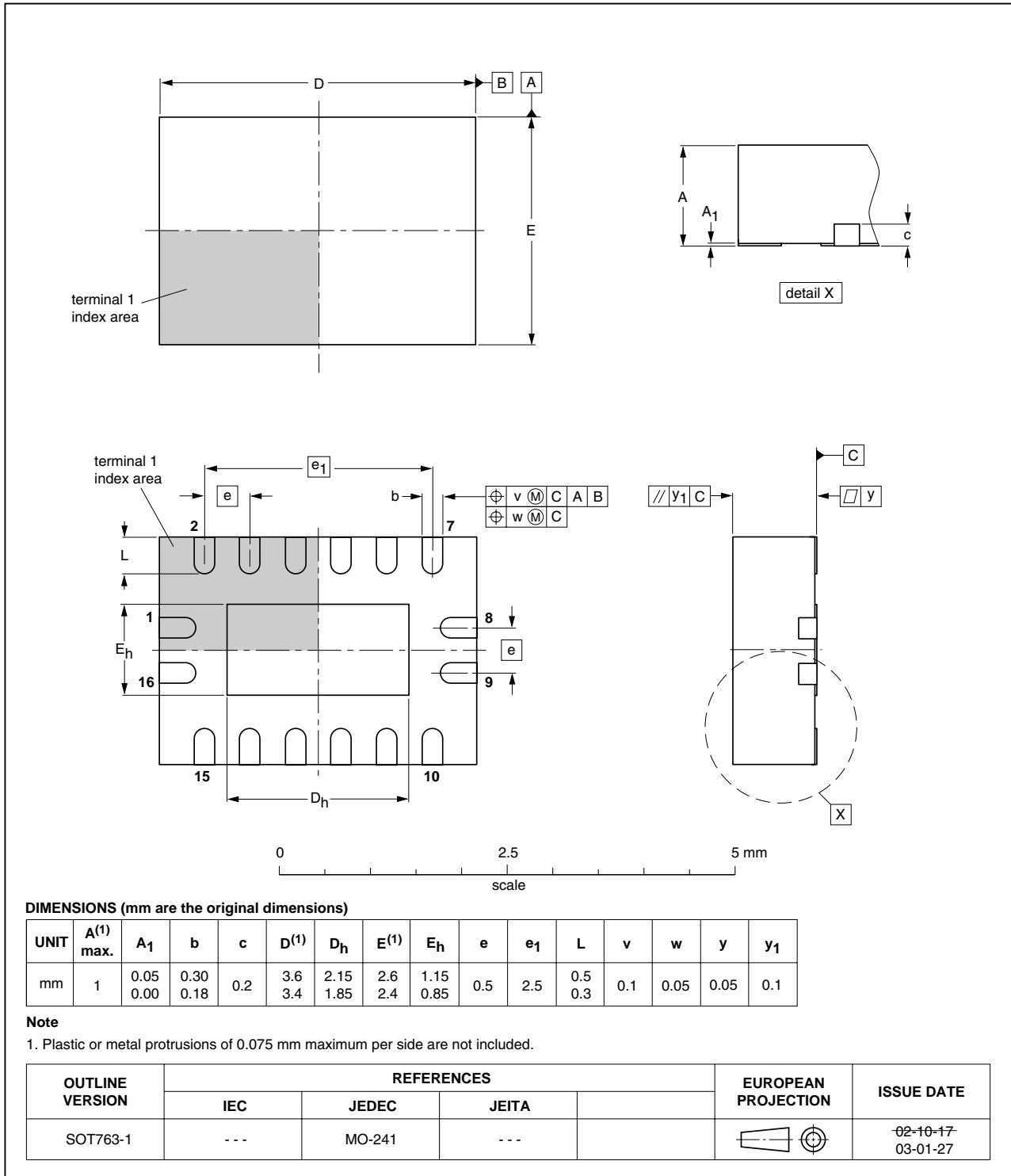


Fig 20. Package outline SOT763-1 (DHVQFN16)

13. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74CBTLV3253_1	20100108	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

15.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

16. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

17. Contents

1 General description 1

2 Features 1

3 Ordering information 2

4 Functional diagram 2

5 Pinning information 3

5.1 Pinning 3

5.2 Pin description 3

6 Functional description 4

7 Limiting values 4

8 Recommended operating conditions 4

9 Static characteristics 5

9.1 Test circuits 5

9.2 ON resistance 6

9.3 ON resistance test circuit and graphs 6

10 Dynamic characteristics 9

11 Waveforms 10

12 Package outline 12

13 Abbreviations 16

14 Revision history 16

15 Legal information 17

15.1 Data sheet status 17

15.2 Definitions 17

15.3 Disclaimers 17

15.4 Trademarks 17

16 Contact information 17

17 Contents 18

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



© NXP B.V. 2010.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 8 January 2010

Document identifier: 74CBTLV3253_1